

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

147 papers	3,613 citations	31 h-index	57 g-index
165 ext. papers	3,884 ext. citations	4.1 avg, IF	4.81 L-index

#	Paper	IF	Citations
147	Nanowire-based one-dimensional electronics. <i>Materials Today</i> , <b>2006</b> , 9, 28-35	21.8	587
146	M-plane core-shell InGaN/GaN multiple-quantum-wells on GaN wires for electroluminescent devices. <i>Nano Letters</i> , <b>2011</b> , 11, 4839-45	11.5	172
145	Self-assembled growth of catalyst-free GaN wires by metal-organic vapour phase epitaxy. <i>Nanotechnology</i> , <b>2010</b> , 21, 015602	3.4	167
144	Flexible Light-Emitting Diodes Based on Vertical Nitride Nanowires. <i>Nano Letters</i> , <b>2015</b> , 15, 6958-64	11.5	149
143	Integrated photonic platform based on InGaN/GaN nanowire emitters and detectors. <i>Nano Letters</i> , <b>2014</b> , 14, 3515-20	11.5	148
142	Composition of Wide Bandgap Semiconductor Materials and Nanostructures Measured by Atom Probe Tomography and Its Dependence on the Surface Electric Field. <i>Journal of Physical Chemistry C</i> , <b>2014</b> , 118, 24136-24151	3.8	114
141	Homoepitaxial growth of catalyst-free GaN wires on N-polar substrates. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 151909	3.4	108
140	Surface diffusion dewetting of thin solid films: Numerical method and application to Si/SiO <sub>2</sub> . <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	87
139	Flexible White Light Emitting Diodes Based on Nitride Nanowires and Nanophosphors. <i>ACS Photonics</i> , <b>2016</b> , 3, 597-603	6.3	72
138	Ordering of Ge quantum dots with buried Si dislocation networks. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 3078-3080	3.1	66
137	Analysis of strain and stacking faults in single nanowires using Bragg coherent diffraction imaging. <i>New Journal of Physics</i> , <b>2010</b> , 12, 035013	2.9	64
136	Correlation of microphotoluminescence spectroscopy, scanning transmission electron microscopy, and atom probe tomography on a single nano-object containing an InGaN/GaN multiquantum well system. <i>Nano Letters</i> , <b>2014</b> , 14, 107-14	11.5	63
135	Single-wire photodetectors based on InGaN/GaN radial quantum wells in GaN wires grown by catalyst-free metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 233107	3.4	59
134	Strain and shape of epitaxial InAs/InP nanowire superlattice measured by grazing incidence X-ray techniques. <i>Nano Letters</i> , <b>2007</b> , 7, 2596-601	11.5	56
133	X-ray scattering study of hydrogen implantation in silicon. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 103509	2.5	56
132	Inversion Domain Boundaries in GaN Wires Revealed by Coherent Bragg Imaging. <i>ACS Nano</i> , <b>2015</b> , 9, 9210-6	16.7	54
131	Single-Wire Light-Emitting Diodes Based on GaN Wires Containing Both Polar and Nonpolar InGaN/GaN Quantum Wells. <i>Applied Physics Express</i> , <b>2012</b> , 5, 014101	2.4	54

130	Accurate control of the misorientation angles in direct wafer bonding. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 793-795	3-4	54
129	Flexible Photodiodes Based on Nitride Core/Shell p-n Junction Nanowires. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 26198-26206	9-5	52
128	Enhanced Sb incorporation in InAsSb nanowires grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 113104	3-4	49
127	Effect of the quantum well thickness on the performance of InGaN photovoltaic cells. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 131105	3-4	47
126	Light emitting diodes based on GaN core/shell wires grown by MOVPE on n-type Si substrate. <i>Electronics Letters</i> , <b>2011</b> , 47, 765-767	1-1	47
125	Two-dimensional electron-hole liquid in single Si quantum wells with large electronic and dielectric confinement. <i>Physical Review Letters</i> , <b>2004</b> , 92, 236802	7-4	39
124	M-Plane GaN/InAlN Multiple Quantum Wells in CoreShell Wire Structure for UV Emission. <i>ACS Photonics</i> , <b>2014</b> , 1, 38-46	6-3	37
123	Catalyst-free growth of high-optical quality GaN nanowires by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 251910	3-4	36
122	Controlled surface nanopatterning with buried dislocation arrays. <i>Surface Science</i> , <b>2003</b> , 545, 211-219	1-8	35
121	High-energy x-ray reflectivity of buried interfaces created by wafer bonding. <i>Physical Review B</i> , <b>2001</b> , 63,	3-3	33
120	Investigation of Photovoltaic Properties of Single Core-Shell GaN/InGaN Wires. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 21898-906	9-5	32
119	Coherent x-ray wavefront reconstruction of a partially illuminated Fresnel zone plate. <i>Optics Express</i> , <b>2011</b> , 19, 19223-32	3-3	32
118	Quantum communication with quantum dot spins. <i>Physical Review B</i> , <b>2007</b> , 75,	3-3	32
117	Surface segregation in binary Cu-Ni and Pt-Ni alloys using Monte Carlo simulation. <i>Surface Science</i> , <b>1990</b> , 231, 419-426	1-8	32
116	PyNX.Ptycho: a computing library for X-ray coherent diffraction imaging of nanostructures. <i>Journal of Applied Crystallography</i> , <b>2016</b> , 49, 1842-1848	3-8	30
115	Experimental and theoretical analysis of transport properties of core-shell wire light emitting diodes probed by electron beam induced current microscopy. <i>Nanotechnology</i> , <b>2014</b> , 25, 255201	3-4	30
114	Coherent-diffraction imaging of single nanowires of diameter 95 nanometers. <i>Physical Review B</i> , <b>2009</b> , 79,	3-3	27
113	Wafer-scale selective area growth of GaN hexagonal prismatic nanostructures on c-sapphire substrate. <i>Journal of Crystal Growth</i> , <b>2011</b> , 322, 15-22	1-6	27

112	Metal organic vapour-phase epitaxy growth of GaN wires on Si (111) for light-emitting diode applications. <i>Nanoscale Research Letters</i> , <b>2013</b> , 8, 61	5	25
111	Elastic relaxation in patterned and implanted strained silicon on insulator. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 114302	2.5	25
110	Exploring single semiconductor nanowires with a multimodal hard X-ray nanoprobe. <i>Advanced Materials</i> , <b>2014</b> , 26, 7873-9	24	24
109	Multi-microscopy study of the influence of stacking faults and three-dimensional In distribution on the optical properties of m-plane InGa <sub>N</sub> quantum wells grown on microwire sidewalls. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 042102	3.4	23
108	Flexible Capacitive Piezoelectric Sensor with Vertically Aligned Ultralong GaN Wires. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 4794-4800	9.5	22
107	Dislocation strain field in ultrathin bonded silicon wafers studied by grazing incidence x-ray diffraction. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	22
106	Equilibrium Shape of Steps and Islands on Polar II-VI Semiconductors Surfaces. <i>Physical Review Letters</i> , <b>1999</b> , 83, 2366-2369	7.4	22
105	Photovoltaic Response of InGa <sub>N</sub> /Ga <sub>N</sub> Multiple-Quantum Well Solar Cells. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JH05	1.4	21
104	Ultra thin silicon films directly bonded onto silicon wafers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 73, 42-46	3.1	21
103	Electronic and optical properties of Si <sub>3</sub> BiO <sub>2</sub> nanostructures. I. Electron-hole collective processes in single Si <sub>3</sub> BiO <sub>2</sub> quantum wells. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	20
102	Epitaxial growth of CdTe(0 0 1) studied by scanning tunnelling microscopy. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 203-207	1.6	18
101	Electronic and optical properties of Si <sub>3</sub> BiO <sub>2</sub> nanostructures. II. Electron-hole recombination at the Si <sub>3</sub> BiO <sub>2</sub> quantum-well/quantum-dot transition. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	18
100	Green Electroluminescence from Radial m-Plane InGa <sub>N</sub> Quantum Wells Grown on Ga <sub>N</sub> Wire Sidewalls by MetalOrganic Vapor Phase Epitaxy. <i>ACS Photonics</i> , <b>2018</b> , 5, 4330-4337	6.3	18
99	Improved conversion efficiency of as-grown InGa <sub>N</sub> /Ga <sub>N</sub> quantum-well solar cells for hybrid integration. <i>Applied Physics Express</i> , <b>2014</b> , 7, 032301	2.4	17
98	X-ray reflectivity of ultrathin twist-bonded silicon wafers. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3509-3511	3.4	17
97	Effect of the barrier thickness on the performance of multiple-quantum-well InGa <sub>N</sub> photovoltaic cells. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 072302	1.4	16
96	Dependence of the photovoltaic performance of pseudomorphic InGa <sub>N</sub> /Ga <sub>N</sub> multiple-quantum-well solar cells on the active region thickness. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 161907	3.4	16
95	Electrical and diffraction characterization of short and narrow MOSFETs on fully depleted strained silicon-on-insulator (sSOI). <i>Solid-State Electronics</i> , <b>2010</b> , 54, 861-869	1.7	15

94	MBE growth of Fe(211)/Au(110) multilayers on MgO(110) substrates. <i>Journal of Magnetism and Magnetic Materials</i> , <b>1993</b> , 121, 57-59	2.8	15
93	InGaN/GaN core/shell nanowires for visible to ultraviolet range photodetection. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 936-940	1.6	15
92	Silane-Induced N-Polarity in Wires Probed by a Synchrotron Nanobeam. <i>Nano Letters</i> , <b>2017</b> , 17, 946-952	11.5	14
91	Substrate-Free InGaN/GaN Nanowire Light-Emitting Diodes. <i>Nanoscale Research Letters</i> , <b>2015</b> , 10, 447	5	14
90	GaN wire-based Langmuir-Blodgett films for self-powered flexible strain sensors. <i>Nanotechnology</i> , <b>2014</b> , 25, 375502	3.4	14
89	Anisotropic relaxation during the first stages of the growth of ZnTe/(001) CdTe strained layers studied by reflection high energy electron diffraction. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3456-3458	3.4	14
88	A first-principles phase stability study on the Au-Ni system. <i>Journal of Physics Condensed Matter</i> , <b>1994</b> , 6, L47-L52	1.8	14
87	Study of the first-stage relaxation in ZnTe/(001)CdTe strained layers. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 3631-3633	3.4	14
86	The Growth of Ni Overlayers on Au(100) Buffers Deposited on GaAs(100) and MgO(100) Substrates.. <i>Materials Research Society Symposia Proceedings</i> , <b>1991</b> , 237, 511		14
85	Au-Ni solid solutions studied by numerical relaxation. <i>Journal De Physique, I</i> , <b>1993</b> , 3, 787-802		14
84	Molecular beam epitaxial growth of Au(110) layers on MgO(110) substrates. <i>Applied Surface Science</i> , <b>1993</b> , 68, 203-207	6.7	13
83	Comprehensive analyses of core-shell InGaN/GaN single nanowire photodiodes. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 484001	3	12
82	Role of Underlayer for Efficient Core-Shell InGaN QWs Grown on -plane GaN Wire Sidewalls. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 19092-19101	9.5	12
81	Nanometric artificial structuring of semiconductor surfaces for crystalline growth. <i>Comptes Rendus Physique</i> , <b>2005</b> , 6, 105-116	1.4	12
80	Investigation of the epitaxial growth mechanism of ZnTe on (001) CdTe. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 3104-3110	2.5	12
79	Crystallographic orientation of facets and planar defects in functional nanostructures elucidated by nano-focused coherent diffractive X-ray imaging. <i>Nanoscale</i> , <b>2018</b> , 10, 4833-4840	7.7	11
78	Self-organized and self-catalyst growth of semiconductor and metal wires by vapour phase epitaxy: GaN rods versus Cu whiskers. <i>Comptes Rendus Physique</i> , <b>2013</b> , 14, 221-227	1.4	11
77	X-ray measurements of the strain and shape of dielectric/metallic wrap-gated InAs nanowires. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 131911	3.4	11

76	Growth of Ge on Si(001) studied in situ by grazing incidence small angle X-ray scattering. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e2195-e2200	1.6	11
75	Nanometric patterning with ultrathin twist bonded silicon wafers. <i>Thin Solid Films</i> , <b>2000</b> , 380, 10-14	2.2	11
74	Optical properties of single non-polar GaN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2006</b> , 243, 1652-1656	1.3	10
73	Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. <i>Nano Letters</i> , <b>2017</b> , 17, 3347-3355	11.5	9
72	Fully Depleted Strained Silicon-on-Insulator p-MOSFETs With Recessed and Embedded Silicon/Germanium Source/Drain. <i>IEEE Electron Device Letters</i> , <b>2010</b> , 31, 1074-1076	4.4	9
71	Grazing incidence x-ray scattering investigation of Si surface patterned with buried dislocation networks. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 2598-2600	3.4	9
70	Toward two-dimensional self-organization of nanostructures using wafer bonding and nanopatterned silicon surfaces. <i>IEEE Journal of Quantum Electronics</i> , <b>2002</b> , 38, 995-1005	2	9
69	Grazing incidence X-ray studies of twist-bonded Si/Si and Si/SiO <sub>2</sub> interfaces. <i>Physica B: Condensed Matter</i> , <b>2000</b> , 283, 103-107	2.8	9
68	Time-dependent relaxation of strained silicon-on-insulator lines using a partially coherent x-ray nanobeam. <i>Physical Review Letters</i> , <b>2013</b> , 111, 215502	7.4	8
67	Impact of Mobility Boosters (XsSOI, CESL, TiN gate) on the Performance of or oriented FDSOI CMOSFETs for the 32nm Node <b>2007</b> ,		8
66	Controlled Ge quantum dots positioning with nano-patterned Si(001) substrates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2006</b> , 243, 3963-3967	1.3	8
65	Interface dilution and morphology of CdTe/MnTe superlattices studied by small angle X-ray scattering. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 109-113	1.6	7
64	(001) silicon surfacial grain boundaries obtained by direct wafer bonding process: accurate control of the structure before bonding. <i>Philosophical Magazine</i> , <b>2005</b> , 85, 2415-2448	1.6	7
63	Ge quantum dots growth on nanopatterned Si(001) surface: Morphology and stress relaxation study. <i>Surface Science</i> , <b>2006</b> , 600, 3187-3193	1.8	7
62	UV Emission from GaN Wires with -Plane Core-Shell GaN/AlGaIn Multiple Quantum Wells. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 44007-44016	9.5	7
61	Radiation sensors based on GaN microwires. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 175105	3	6
60	InGaIn/GaN multiple-quantum well heterostructures for solar cells grown by MOVPE: case studies. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 350-354		6
59	Orientation-Dependent Dewetting of Patterned Thin Si Film on SiO <sub>2</sub> . <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 910, 5		6

58	Interface dilution and morphology of CdTe/MnTe superlattices studied by small- and large-angle x-ray scattering. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 7266-7274	2.5	5
57	Large and small angle x-ray scattering studies of CdTe/MgTe superlattices. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 1951-1957	2.5	5
56	Nitride Nanowires for Light Emitting Diodes. <i>Solid State Lighting Technology and Application Series</i> , <b>2019</b> , 425-484	0.7	5
55	Towards simulation at picometer-scale resolution: Revisiting inversion domain boundaries in GaN. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	5
54	Carrier dynamics near a crack in GaN microwires with AlGaIn multiple quantum wells. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 221105	3.4	4
53	Thermal Evolution of Implantation Damages in Mg-Implanted GaN Layers Grown on Si. <i>ECS Transactions</i> , <b>2017</b> , 80, 131-138	1	4
52	Growth and characterization of ZnO nanowires on p-type GaN. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 250-252	2.8	4
51	Width and orientation effects in strained FDSOI MOSFETs: strain and device characterization <b>2009</b> ,		4
50	Interface roughness correlation in CdTe/CdZnTe strained quantum wells. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 886-889	1.6	4
49	GIXRD of nanoscale strain patterning in wafer bonding. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2003</b> , 200, 73-78	1.2	4
48	Dislocation Networks Strain Fields Induced By Si Wafer Bonding. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 673, 1		4
47	A helium mini-cryostat for the nanoprobe beamline ID16B at ESRF: characteristics and performance. <i>Journal of Synchrotron Radiation</i> , <b>2020</b> , 27, 1074-1079	2.4	4
46	Mapping Inversion Domain Boundaries along Single GaN Wires with Bragg Coherent X-ray Imaging. <i>ACS Nano</i> , <b>2020</b> , 14, 10305-10312	16.7	4
45	Piezo-Potential Generation in Capacitive Flexible Sensors Based on GaN Horizontal Wires. <i>Nanomaterials</i> , <b>2018</b> , 8,	5.4	3
44	Colour optimization of phosphor-converted flexible nitride nanowire white light emitting diodes. <i>JPhys Photonics</i> , <b>2019</b> , 1, 035003	2.5	3
43	Capping stability of Mg-implanted GaN layers grown on silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600487	1.6	3
42	Determination of the biaxial stress in strained silicon nano-strips through polarized oblique incidence Raman spectroscopy. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 164309	2.5	3
41	Direct Wafer Bonding for Nanostructure Preparations. <i>Solid State Phenomena</i> , <b>2007</b> , 121-123, 29-32	0.4	3



40	STM study of ultra-thin (. <i>Journal of Non-Crystalline Solids</i> , <b>2003</b> , 322, 174-178	3.9	3
39	Determination de contraintes résiduelles en incidence rasante. Apport du rayonnement synchrotron. <i>European Physical Journal Special Topics</i> , <b>2000</b> , 10, Pr10-103-Pr10-113		3
38	Extended synchrotron X-ray reflectivity study of a Sm-based layer buried into CdTe(001). <i>Surface Science</i> , <b>1995</b> , 327, L515-L520	1.8	3
37	In situ characterization of rare earth-CdTe heterostructures by ion beam analysis. <i>Thin Solid Films</i> , <b>1994</b> , 249, 266-270	2.2	3
36	XTOP: high-resolution X-ray diffraction and imaging. <i>Journal of Applied Crystallography</i> , <b>2015</b> , 48, 620	3.8	2
35	Fully depleted Silicon-On-Insulator with back bias and strain for low power and high performance applications <b>2010</b> ,		2
34	Nanoscaled MOSFET Transistors on Strained Si, SiGe, Ge Layers: Some Integration and Electrical Properties Features. <i>ECS Transactions</i> , <b>2006</b> , 3, 947-961	1	2
33	X-ray reflectivity of silicon on insulator wafers. <i>Materials Science in Semiconductor Processing</i> , <b>2001</b> , 4, 31-33	4.3	2
32	Large and small angle x-ray scattering studies of Si/SiGe superlattices grown by gas-source molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 198-204	1.8	2
31	A study of the strain distribution by scanning X-ray diffraction on GaP/Si for III/V monolithic integration on silicon. <i>Journal of Applied Crystallography</i> , <b>2019</b> , 52, 809-815	3.8	2
30	Stretchable Transparent Light-Emitting Diodes Based on InGaN/GaN Quantum Well Microwires and Carbon Nanotube Films. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	2
29	Flexible optoelectronic devices based on nitride nanowires embedded in polymer films <b>2016</b> ,		2
28	Nitride nanowire light emitting diodes <b>2015</b> ,		1
27	X-ray-diffraction study of the lattice distortions induced by a fractional monolayer:ZnTe embedded in vicinal CdTe(001). <i>Physical Review B</i> , <b>1997</b> , 55, 15804-15812	3.3	1
26	Surface Evolution of Strained Thin Solid Films: Stability Analysis and Time Evolution of Local Surface Perturbations <b>2007</b> ,		1
25	Buried hydrophobic silicon bonding studied by high-energy x-ray reflectivity. <i>Journal Physics D: Applied Physics</i> , <b>2003</b> , 36, A205-A208	3	1
24	Germanium growth on nanopatterned surface studied by STM. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e1605-e1613	1.6	1
23	Electron hole liquid in silicon single quantum wells. <i>Optical Materials</i> , <b>2005</b> , 27, 995-999	3.3	1



22	Photoluminescence of nanometric single silicon quantum wells. <i>Optical Materials</i> , <b>2005</b> , 27, 1000-1003	3.3	1
21	Co-integrated dual strained channels on fully depleted sSDOI CMOSFETs with HfO <sub>2</sub> /TiN gate stack down to 15nm gate length		1
20	Stress measurements in thin zirconia films at 300°C using synchrotron radiation. <i>Journal of Neutron Research</i> , <b>2001</b> , 9, 263-272	0.5	1
19	X-ray Reflectivity Study of Porous Silicon Formation. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 536, 293		1
18	An Auger depth profile analysis of a sputtered Fe-Ti multilayer structure. <i>Applied Surface Science</i> , <b>1991</b> , 47, 127-138	6.7	1
17	Heat Dissipation in Flexible Nitride Nanowire Light-Emitting Diodes. <i>Nanomaterials</i> , <b>2020</b> , 10,	5.4	1
16	Ion beam induced current analysis in GaN microwires. <i>EPJ Web of Conferences</i> , <b>2020</b> , 233, 05001	0.3	1
15	Dual-Color Emission from Monolithic m-Plane CoreShell InGaN/GaN Quantum Wells. <i>Advanced Photonics Research</i> , <b>2021</b> , 2, 2000148	1.9	1
14	Self-powered proton detectors based on GaN core-shell p-n microwires. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 193501	3.4	1
13	Optical properties of photodetectors based on single GaN nanowires with a transparent graphene contact. <i>Semiconductors</i> , <b>2016</b> , 50, 1097-1101	0.7	1
12	Scanning x-ray microscopy imaging of strain relaxation and fluctuations in thin patterned SiGe-on-insulator nanostructures. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 095302	2.5	1
11	Diffusion and Aggregation of Mg Implanted in GaN on Si <b>2018</b> ,		1
10	Growth of GaN-based nanorod heterostructures (core-shell) for optoelectronics and their nanocharacterization <b>2015</b> , 323-335		
9	Picometre-precision atomic structure of inversion domain boundaries in GaN <b>2016</b> , 564-565		
8	Metal-Organic Vapor Phase Epitaxy Growth of GaN Nanorods <b>2014</b> , 245-264		
7	Metal positioning on silicon surfaces using the etching of buried dislocation arrays. <i>Nanotechnology</i> , <b>2011</b> , 22, 215301	3.4	
6	Controlled Silicon (001) Surface Periodic Nanopatterning by Direct Wafer Bonding. <i>ECS Transactions</i> , <b>2006</b> , 3, 261-267	1	
5	Localized destructive interference in X-ray specular reflectivity. <i>Journal of Applied Crystallography</i> , <b>1999</b> , 32, 859-863	3.8	

- 4 Stress and Strain Measurement in Stressed Silicon Lines. *Springer Proceedings in Physics*, **2008**, 419-422 0.2
- 3 Spatially and Time-Resolved Carrier Dynamics in Core-Shell InGaN/GaN Multiple-Quantum Wells on GaN Wire. *Nano Letters*, **2021**, 21, 9494-9501 11.5
- 2 Detailed geometrical characterisation of a surfacial Si (100) grain boundary **2018**, 425-428
- 1 Semiconductor Templates for the Fabrication of Nano-Objects 169-188